

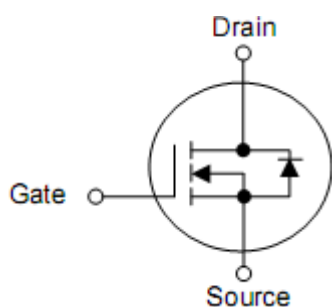
1. Features

- $R_{DS(ON)}=4.3m\Omega(\text{typ.})@V_{GS}=10V, \text{DFN}3*3/\text{DFN}5*6$
- $R_{DS(ON)}=4.5m\Omega(\text{typ.})@V_{GS}=10V, \text{TO-252}/\text{TO-263}$
- Very Low On-resistance $R_{DS(ON)}$
- Low C_{rss}
- Fast switching
- 100% avalanche tested
- Improved dv/dt capability

2. Applications

- PWM Application
- Power Management
- Load switch

3. Symbol



Pin		Function
DFN3*3/DFN5*6	TO-252/TO-263	
4	1	Gate
5,6,7,8	2	Drain
1,2,3	3	Source

5. Ordering Information

Part Number	Package	Brand
KNG3403C	DFN3*3	KIA
KNY3403C	DFN5*6	KIA
KND3403C	TO-252	KIA
KNB3403C	TO-263	KIA

6. Absolute maximum ratings

$T_C=25^{\circ}\text{C}$ unless otherwise noted

Parameter		Symbol	Rating		Units
			DNF3*3 DFN5*6	TO-252 TO-263	
Drain-source voltage		V_{DSS}	30		V
Continuous drain current	$T_C=25^{\circ}\text{C}$	I_D	80		A
	$T_C=100^{\circ}\text{C}$	I_D	45		A
Pulsed drain current	-Pulsed ¹⁾	I_{DM}	320		A
Gate-source voltage		V_{GS}	± 20		V
Single pulse avalanche energy ²⁾		E_{AS}	306		mJ
Power dissipation ($T_C=25^{\circ}\text{C}$)		P_D	70	83	W
Operating junction and storage temperature range		T_J, T_{STG}	-55 to 150		$^{\circ}\text{C}$
Maximum lead temperature for soldering purposes, 1/8" from case for 5 seconds		T_L	300		$^{\circ}\text{C}$

*Drain current limited by maximum junction temperature.

7. Thermal characteristics

Parameter	Symbol	Rating		Unit
		DFN3*3/DFN5*6	TO-252/TO-263	
Thermal resistance junction-case	$R_{\theta JC}$	1.8	1.5	$^{\circ}\text{C/W}$

8. Electrical characteristics

(T_C=25°C unless otherwise noted)

Parameter	Symbol	Test Conditions		Min	Typ	Max	Units
Drain-source breakdown voltage	BV _{DSS}	V _{GS} =0V, I _D =250uA		30	-	-	V
Drain-source leakage current	I _{DSS}	V _{DS} =30V, V _{GS} =0V		-	-	1	uA
Gate-source forward leakage	I _{GSS}	V _{GS} =±20V, V _{DS} =0V		-	-	±100	nA
Gate threshold voltage	V _{GS(TH)}	V _{DS} = V _{GS} , I _D =250uA		1.0	1.6	2.2	V
Drain-source on-resistance	R _{DS(on)}	V _{GS} =10V, I _D =20A	DFN3*3/DFN5*6	-	4.3	6.0	mΩ
			TO-252/TO-263	-	4.5	6.0	mΩ
		V _{GS} =4.5V, I _D =20A	DFN3*3/DFN5*6	-	6.7	9.2	mΩ
			TO-252/TO-263		7.5	9.2	mΩ
Input capacitance	C _{iss}	V _{DS} =15V, V _{GS} =0V f=1MHz		-	1972	-	pF
Output capacitance	C _{oss}			-	214	-	pF
Reverse transfer capacitance	C _{rss}			-	176	-	pF
Turn-on delay time	t _{d(on)}	V _{GS} =10V, V _{DS} =15V, R _G =2.7Ω, I _D =30A ³⁾		-	21	-	ns
Rise time	t _r			-	16	-	ns
Turn-off delay time	t _{d(off)}			-	62	-	ns
Fall time	t _f			-	12	-	ns
Total gate charge(10V)	Q _g	V _{DS} =15V, I _D =30A V _{GS} =10V ³⁾		-	37.2	-	nC
Gate-source charge	Q _{gs}			-	5.7	-	nC
Gate-drain charge	Q _{gd}			-	7.6	-	nC
Maximum Continuous Drain-Source Diode Forward Current	I _S	—		-	-	80	A
Maximum Pulsed Drain-Source Diode Forward Current	I _{SM}	—		-	-	320	A
Diode forward voltage	V _{SD}	I _{SD} =30A, V _{GS} =0V, T _J =25°C		-	-	1.2	V
Reverse Recovery Time	t _{rr}	I _F =80A, di/dt=100A/μs T _J =25°C		-	32	-	nS
Reverse Recovery Charge	Q _{rr}			-	12	-	nC

Note:

1) Repetitive Rating: Pulse Width Limited by Maximum Junction Temperature

2) EAS condition: T_J=25°C, V_{DD}=15V, V_G=10V, L=0.5mH, R_G=25Ω

3) Pulse Test: Pulse Width≤300μs, Duty Cycle≤0.5%

9. Typical operating characteristics

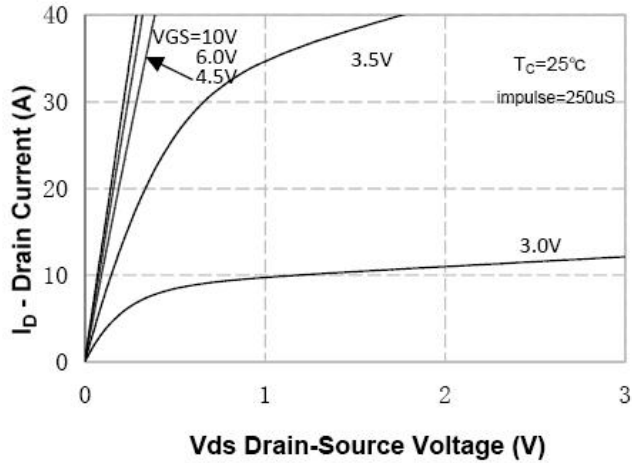


Figure 1. On-Region Characteristics

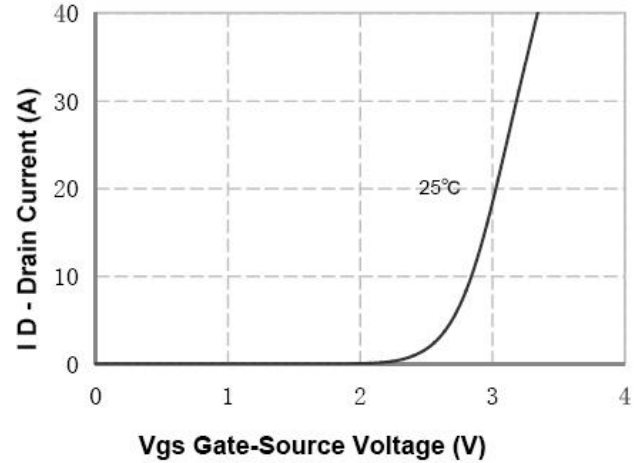


Figure 2. Transfer Characteristics

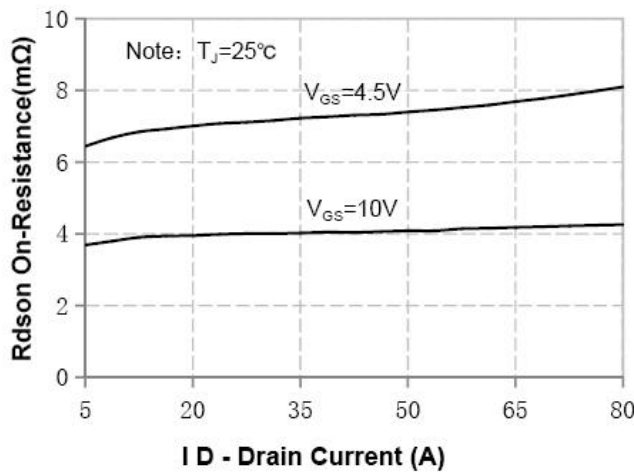


Figure 3. On-Resistance Variation vs Drain Current and Gate Voltage

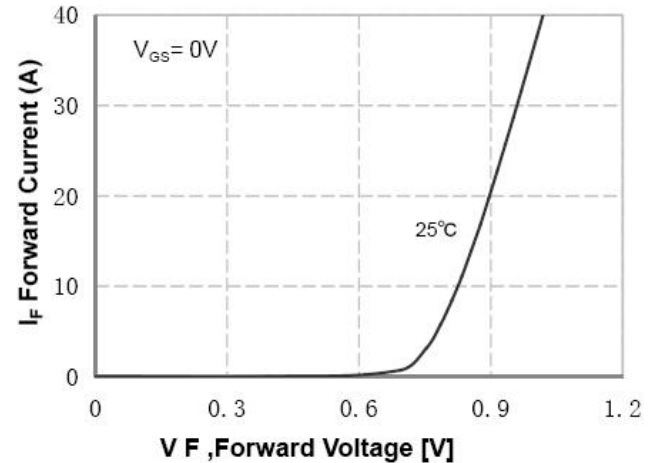


Figure 4. Body Diode Forward Voltage Variation vs Source Current

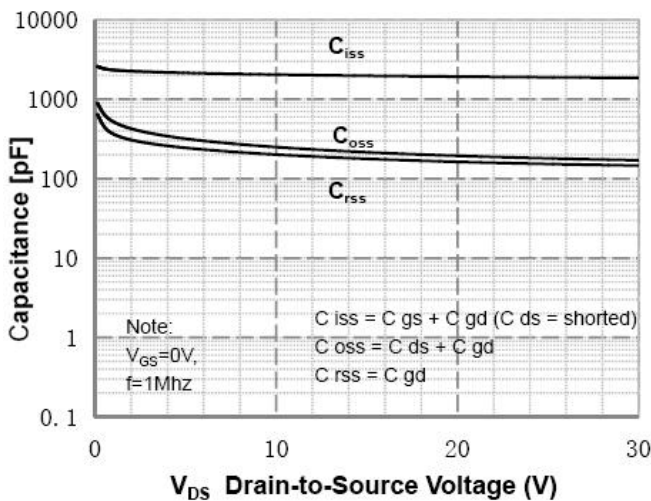


Figure 5. Capacitance Characteristics

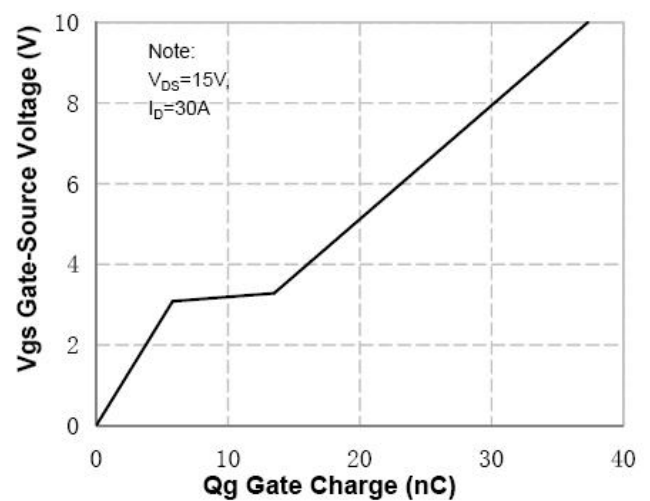


Figure 6. Gate Charge Characteristics

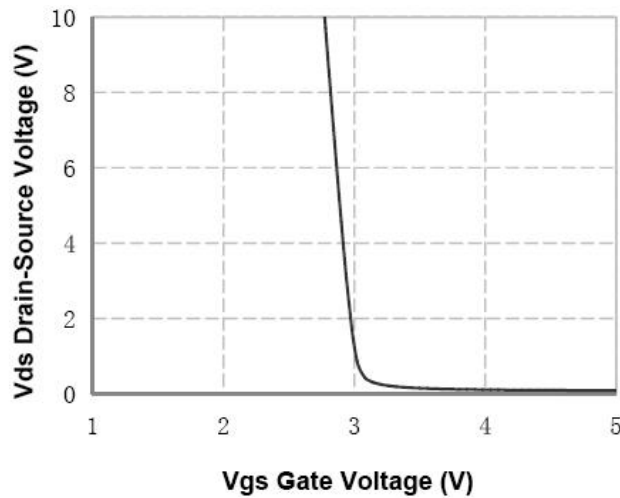


Figure 7. Vds Drain-Source Voltage vs Gate Voltage

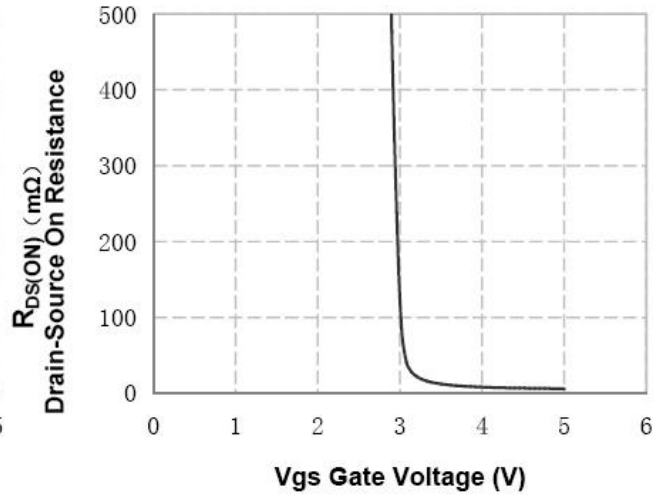


Figure 8. On-Resistance vs Gate Voltage

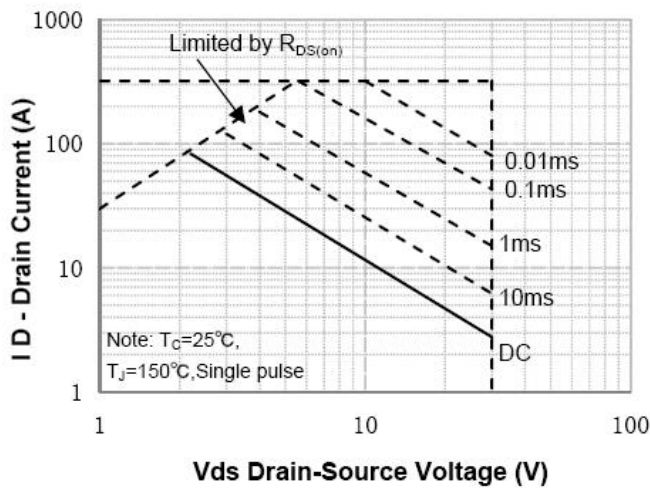


Figure 9. Maximum Safe Operating Area

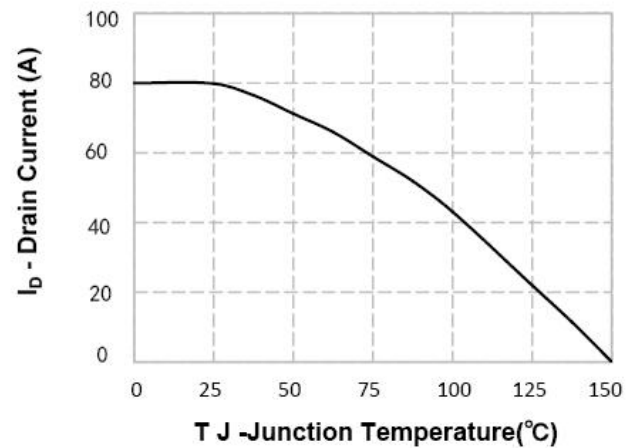


Figure 10. Maximum Continuous Drain Current vs Case Temperature

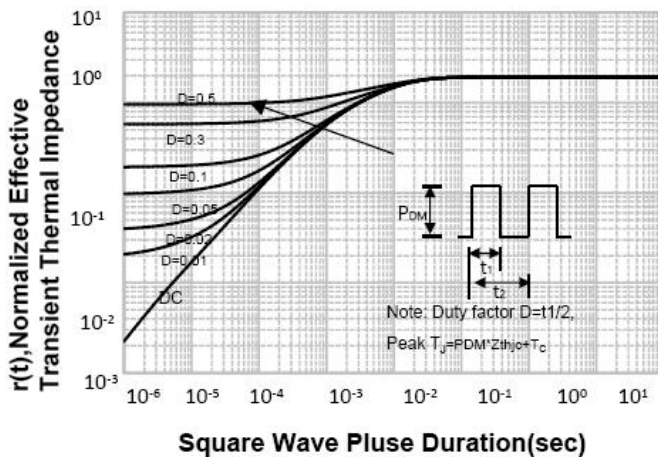
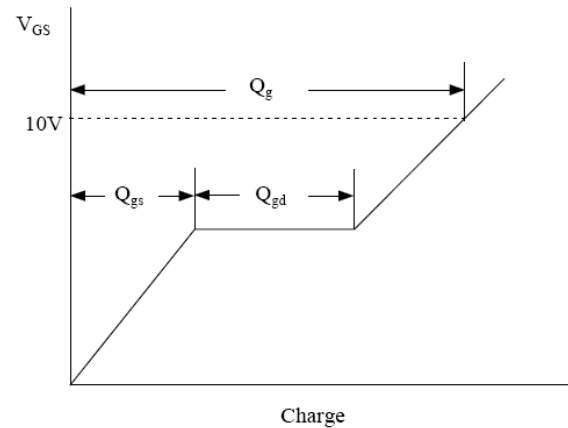
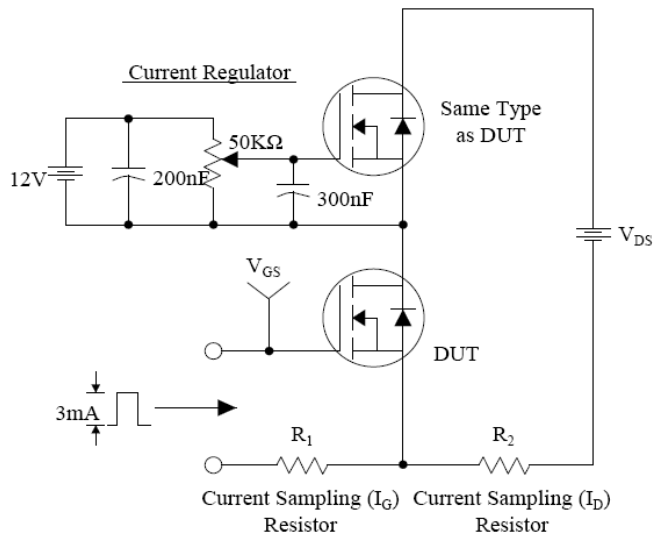


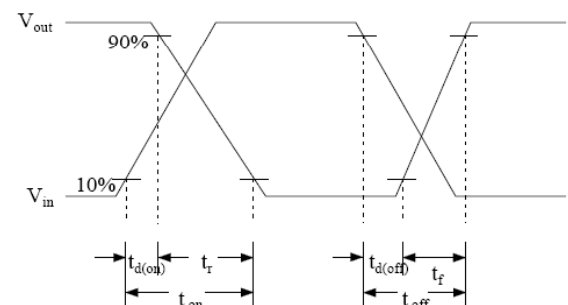
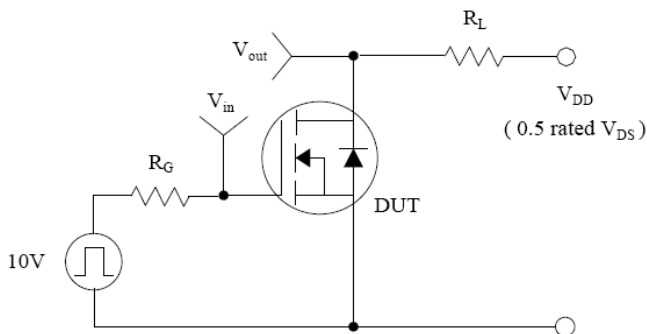
Figure 11. Transient Thermal Response Curve

10. Test Circuits and Waveforms

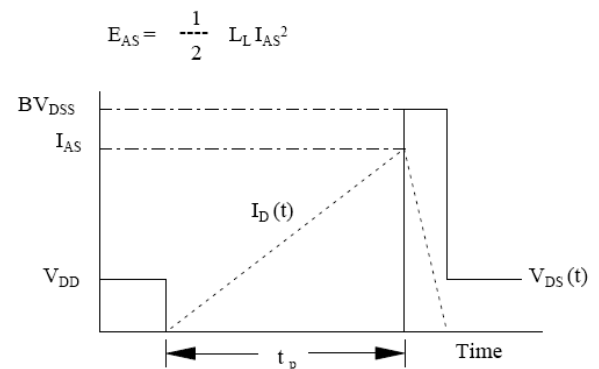
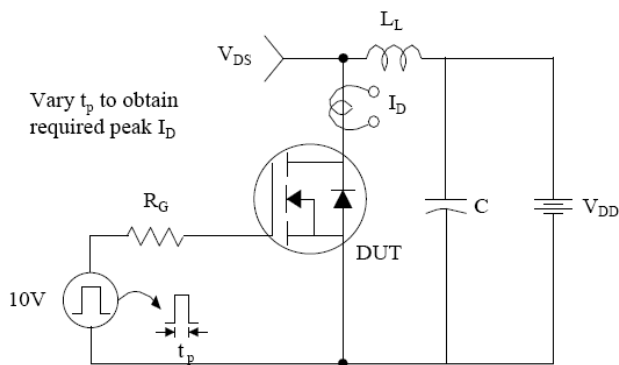
Gate Charge Test Circuit & Waveform



Resistive Switching Test Circuit & Waveforms



Unclamped Inductive Switching Test Circuit & Waveforms



Peak Diode Recovery dv/dt Test Circuit & Waveforms

